L Number	Hits	Search Text	DB	Time stamp
17	2850	(solid near state) and (heat\$4 WITH adhesive)	USPAT;	2003/07/25 08:53
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
24	229	((solid near state) and (heat\$4 WITH adhesive)) and	USPAT	2003/07/25 08:53
24	223	cross near linked	00171	2000/07/20 00:00
25	13	(solid near state with plate) and (heat\$4 WITH	USPAT;	2003/07/25 08:56
25	13	adhesive) and cross near linked	US-PGPUB;	2000/07/20 00:00
		adhesive, and cross hear linked	EPO; JPO;	
			DERWENT:	
			,	
			IBM_TDB	0000/07/05 00.50
32	1	(solid near state) and (heat\$4 WITH adhesive with	USPAT;	2003/07/25 08:58
j		(cross near linked)) and (optical\$5 near2 pump\$4)	US-PGPUB;	
1		and active	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
46	4	(solid near state) and (heat\$4 WITH adhesive with	USPAT;	2003/07/25 09:03
		(cross near linked))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
52	4	(solid near state) and (heat\$4 WITH adhesive with	USPAT;	2003/07/25 09:06
		(cross near linked)) and ((heat neat sink) or cool\$5)	EPO; JPO;	
		(or odd vida. mintody, and fillings vida only, a secret,	DERWENT;	
			IBM TDB	
39	5	(solid near state) and (heat\$4 WITH adhesive with	USPAT;	2003/07/25 09:22
33	3	(cross near linked))	US-PGPUB;	2000/07/20 00:22
		(CIOSS TICAL IIIIKEO))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	•	4 - 15 L	_	2003/07/25 09:26
58	2	(solid near state) and (adhesive with (cross near	USPAT;	2003/07/25 05.20
		linked)) and active and (heat near sink)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
65	12	(solid near state) and (adhesive with (cross near	USPAT;	2003/07/25 09:40
		linked)) and (heat near sink)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
72	0	(solid near state) and (adhesive near (layer or film or	USPAT;	2003/07/25 09:36
		region or medium) with (cross near linked)) and (heat	US-PGPUB;	
		near sink)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
79	29	(solid near state) and (adhesive near (layer or film or	USPAT;	2003/07/25 09:48
-	_5	region or medium) with (cross near linked))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
86	0	(solid near state) and (adhesive with (cross near linked)) SAME (heat near sink)	USPAT;	2003/07/25 09:48
			EPO; JPO;	
		HINCUTT SAIVIE (HEAL HEAL SHIK)	DERWENT;	
92	^	Inclination and to the color and flags of the color	IBM_TDB	2002/07/25 00:50
	0	(solid near state) and (adhesive near (layer or film or	USPAT;	2003/07/25 09:50
		region or medium) with (cross near linked)) and	US-PGPUB;	
		(optical\$5 near pump\$4)	EPO; JPO;	
			DERWENT;	
		I	IBM TDB	ł.

99	289	(solid near state) and (optical\$5 near pump\$4) and (heat near sink)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/25 09:52
107	0	((solid near state) and (optical\$5 near pump\$4) and (heat near sink)) and (adhesive near (layer or film or region or medium) with (cross near linked))	USPAT	2003/07/25 09:54
108	0	((solid near state) and (optical\$5 near pump\$4) and (heat near sink)) and (adhesive with (cross near linked))	USPAT	2003/07/25 09:54
106	238	(solid near state) and (optical\$5 near pump\$4) and (heat near sink)	USPAT	2003/07/25 10:01
109	209	((solid near state) and (optical\$5 near pump\$4) and (heat near sink)) and 372/\$.ccls.	USPAT	2003/07/25 09:59
110	190	(solid near state near laser) and (optical\$5 near pump\$4) and (heat near sink) and 372/\$.ccls.	USPAT	2003/07/25 10:21
111	81	(solid near state near laser) and (optical\$5 near pump\$4) and (heat near sink) and 372/\$.ccls. and amplif\$5	USPAT	2003/07/25 10:23
-	1002	(solid near state) and active and amplif\$5 and cool\$4 and thermal\$5 and heat\$4 and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/02 16:54
-	391	(solid near state) and active and (laser with amplif\$5) and cool\$4 and thermal\$5 and heat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/02 16:59
-	251	((solid near state) and active and (laser with amplif\$5) and cool\$4 and thermal\$5 and heat\$4) and 372/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/02 17:01
-	259	(solid near state near laser) and active and (laser with amplif\$5) and cool\$4 and thermal\$5 and heat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/02 17:01
-	199	((solid near state near laser) and active and (laser with amplif\$5) and cool\$4 and thermal\$5 and heat\$4) and 372/\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/03 10:00
-	154	((solid near state near laser) and active and (laser with amplif\$5) and cool\$4 and thermal\$5 and heat\$4) and liquid and solid and material	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/03 10:03
-	244	((solid near state) and active and (laser with amplif\$5) and cool\$4 and thermal\$5 and heat\$4) and liquid and solid and material	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/03 10:29
-	162	(((solid near state) and active and (laser with amplif\$5) and cool\$4 and thermal\$5 and heat\$4) and liquid and solid and material) and plate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/03 10:24

-	47	((solid near state) and active and (laser with amplif\$5) and cool\$4 and thermal\$5 same heat\$4)	USPAT; US-PGPUB;	2002/12/03 10:35
		and (liquid with solid same material)	EPO; JPO;	
	İ	and (iiquid with solid same material)	DERWENT;	
			IBM TDB	
	55	((solid near state) and active and (laser with	USPAT;	2002/12/03 10:40
_		amplif\$5) and cool\$4 and thermal\$5 and heat\$4)	US-PGPUB;	2002, 12,00 10.10
		and (liquid with solid same material)	EPO; JPO;	
		and finding with solid same material,	DERWENT;	
			IBM TDB	
_	113	(solid near state) and semiconductor and active and	USPAT;	2002/12/03 10:44
		laser and amplif\$5 and cool\$4 and thermal\$5 and	US-PGPUB;	
		heat\$4 and (liquid same solid same material)	EPO; JPO;	
		,	DERWENT;	
			IBM TDB	
_	84	((solid near state) and semiconductor and active and	USPAT;	2002/12/03 15:17
		laser and amplif\$5 and cool\$4 and thermal\$5 and	US-PGPUB;	
		heat\$4 and (liquid same solid same material)) and	EPO; JPO;	
		plate	DERWENT;	
			IBM_TDB	
-	1	((solid near state with plate) and semiconductor and	USPAT;	2002/12/03 15:23
		active and laser and amplif\$5 and cool\$4 and	US-PGPUB;	
		thermal\$5 and heat\$4 and (liquid same solid same	EPO; JPO;	
		material)) and volum\$5	DERWENT;	
			IBM_TDB	
-	8	(((solid near state) with plate) and semiconductor	USPAT;	2002/12/03 15:26
		and active and laser and amplif\$5 and cool\$4 and	US-PGPUB;	
		thermal\$5 and heat\$4 and (liquid AND solid AND	EPO; JPO;	
		material)) and volum\$5	DERWENT;	
			IBM_TDB	
-	20	((solid near state) with plate) and semiconductor and	USPAT;	2002/12/03 15:33
		active and laser and amplif\$5 and cool\$4 and	US-PGPUB;	
		thermal\$5 and heat\$4	EPO; JPO;	
			DERWENT;	
		(Market and a state) CANES alotal and assessment durates	IBM_TDB	2002/12/03 15:36
-	20	(((solid near state) SAME plate) and semiconductor	USPAT;	2002/12/03 15:36
	}	and active and laser and amplif\$5 and cool\$4 and	US-PGPUB; EPO; JPO;	
		thermal\$5 and heat\$4 and (liquid AND solid AND	DERWENT;	
		material)) and volum\$5	IBM TDB	
_	1	(((solid near state) with (body or member or system))	USPAT;	2002/12/03 15:45
	"	and semiconductor and (active near (layer or region	US-PGPUB;	2002/12/00 10:40
		or medium or film)) and (laser with amplif\$5) and	EPO; JPO;	
		(cool\$4 near2 (body or member or system)) and	DERWENT;	
		thermal\$5 and heat\$4 and (liquid AND solid AND	IBM TDB	
		material)) and volum\$5	· · · · · · · · · · · · · · · · · · ·	
-	2	((solid near state) and semiconductor and (active	USPAT;	2002/12/03 15:50
		near (layer or region or medium or film)) and (laser	US-PGPUB;	
		with amplif\$5) and (cool\$4 near2 (body or member	EPO; JPO;	
		or system)) and thermal\$5 and heat\$4 and (liquid	DERWENT;	
1		AND solid AND material)) and volum\$5 and plate	IBM_TDB	
-	1	(((solid near state) with (body or member or system))	USPAT;	2002/12/03 15:54
		and semiconductor and (active near (layer or region	US-PGPUB;	
		or medium or film)) and (laser with amplif\$5) and	EPO; JPO;	
1		(cool\$4 near2 (body or member or system)) and	DERWENT;	
		thermal\$5 and heat\$4 and (liquid AND solid AND	IBM_TDB	
		material)) and volum\$5 and plate		

				,
-	1	((solid near state) and semiconductor and (active	USPAT;	2002/12/03 15:58
		near (layer or region or medium or film)) and (laser	US-PGPUB;	
		with amplif\$5) and cool\$5 and (thermal\$5 near2	EPO; JPO;	
		(body or member or system)) and heat\$4 and	DERWENT;	
		(liquid AND solid AND material)) and volum\$5 and	IBM_TDB	
		plate		
i -	0	(((solid near state) with (body or member or system))	USPAT;	2002/12/03 16:02
		and semiconductor and (active near (layer or region	US-PGPUB;	
		or medium or film)) and (laser with amplif\$5) and	EPO; JPO;	
		cool\$5 and (thermal\$5 near2 (body or member or	DERWENT;	
		system)) and heat\$4 and (liquid AND solid AND	IBM TDB	
		material)) and volum\$5	_	
_	1	((solid near state) and semiconductor and (active	USPAT;	2002/12/03 16:06
	·	near (layer or region or medium or film)) and (laser	US-PGPUB;	
		with amplif\$5) and cool\$5 and (thermal\$5 near2	EPO; JPO;	
		(body or member or system)) and heat\$4 and	DERWENT;	
		(liquid AND solid AND material)) and volum\$5 and	IBM_TDB	
	ا م	plate	LICDAT:	2002/12/03 16:18
-	95	((solid near state) and semiconductor and (active	USPAT;	2002/12/03 10:18
		near (layer or region or medium or film)) and (laser	US-PGPUB;	
		AND amplif\$5) and (cool\$5) and thermal\$5 and	EPO; JPO;	
	!	heat\$4 and (liquid AND solid AND material)) and	DERWENT;	
	_	volum\$5 and plate	IBM_TDB	
-	2	((solid near state) and semiconductor and (active	USPAT;	2002/12/03 16:18
		near (layer or region or medium or film)) and (laser	US-PGPUB;	
		with amplif\$5) and (cool\$5 near2 (body or member	EPO; JPO;	
		or system)) and thermal\$5 and heat\$4 and (liquid	DERWENT;	
		AND solid AND material)) and volum\$5 and plate	IBM_TDB	
-	8	((solid near state) and semiconductor and (active	USPAT;	2002/12/03 16:18
		near (layer or region or medium or film)) and (laser	US-PGPUB;	
		AND amplif\$5) and (cool\$5 near2 (body or member	EPO; JPO;	
		or system)) and thermal\$5 and heat\$4 and (liquid	DERWENT;	
		AND solid AND material)) and volum\$5 and plate	IBM TDB	
_	22	(solid near state) and semiconductor and (active near	USPAT;	2002/12/03 16:27
		(layer or region or medium or film)) and (laser AND	US-PGPUB;	
		amplif\$5) and (cool\$5 near2 (body or member or	EPO; JPO;	
		system)) and heat\$4 and plate	DERWENT;	
		System,, and matrix and plate	IBM TDB	
-	20	(solid near state) and semiconductor and (active near	USPAT;	2002/12/03 16:46
	20	(layer or region or medium or film)) and (laser AND	US-PGPUB;	
		amplif\$5) and (cool\$5 near2 (body or member or	EPO; JPO;	
		system)) and heat\$4 and plate and thermal\$5	DERWENT;	
		Systemy and nearty and plate and the malys	IBM TDB	
1_	15	((solid near state) and semiconductor and (active	USPAT;	2002/12/03 16:40
-	13	near (layer or region or medium or film)) and (laser	US-PGPUB;	2002/12/03 10.40
		•		
		AND amplif\$5) and (cool\$5 near2 (body or member	EPO; JPO;	
		or system)) and heat\$4 and plate and thermal\$5)	DERWENT;	
1	10	and (mirror or reflect\$5)	IBM_TDB	2002/12/02 17 00
-	40	(solid near state) and (active near (layer or region or	USPAT;	2002/12/03 17:06
		medium or film)) and laser and (cool\$5 near2 (body	US-PGPUB;	
		or member or system)) and heat\$4 and plate and	EPO; JPO;	
		thermal\$5 and (mirror or reflect\$5)	DERWENT;	
1		*	IBM_TDB	
-	8	((solid near state) and (active near (layer or region or	USPAT;	2003/07/25 08:49
		medium or film)) and laser and (cool\$5 near2 (body	US-PGPUB;	
		or member or system)) and heat\$4 and plate and	EPO; JPO;	
		thermal\$5 and (mirror or reflect\$5)) and adhesive	DERWENT;	
			IBM_TDB	